

# MG031N110006A

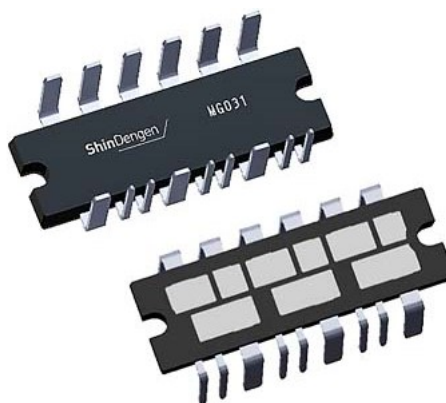
## 3 phase Inverter Module

### Feature

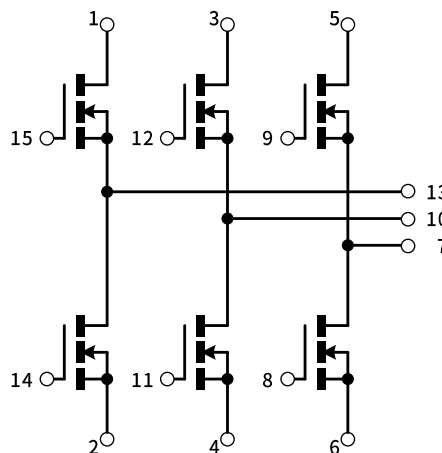
- 3 phase Inverter
- MOSFET(N-channel)
- High current capacity
- Low Ron
- Halogen free
- Pb free terminal
- RoHS:Yes

### Outline

House Name: MG031



### Equivalent circuit



Absolute maximum ratings (Tc = 25°C unless otherwise specified )

MOSFET

| Item                            | Symbol           | Conditions                     | Ratings | Unit |
|---------------------------------|------------------|--------------------------------|---------|------|
| Channel temperature             | Tch              |                                | 175     | °C   |
| Drain-source voltage            | V <sub>DSS</sub> |                                | 60      | V    |
| Gate-source voltage             | V <sub>GSS</sub> |                                | ±20     | V    |
| Continuous drain current (DC)   | I <sub>D</sub>   |                                | 110     | A    |
| Continuous drain current (Peak) | I <sub>DP</sub>  | Pulse width 10μs, Duty = 1/100 | 440     | A    |
| Total power dissipation         | P <sub>T</sub>   |                                | 154     | W    |
| Single avalanche current        | I <sub>AS</sub>  | Starting Tch=25°C Tch≤150°C    | 44      | A    |
| Single avalanche energy         | E <sub>AS</sub>  | Starting Tch=25°C Tch≤150°C    | 232     | mJ   |

Module

| Item                | Symbol | Conditions      | Ratings | Unit |
|---------------------|--------|-----------------|---------|------|
| Storage temperature | Tstg   |                 | -55~150 | °C   |
| Mounting torque     | TOR    | Fixing screw M3 | 0.8     | N・m  |

# Electrical and thermal characteristics (Tc=25°C unless otherwise specified.)

These are characteristics of the 1 chip unless otherwise specified.

## MOSFET

| Item                                       | Symbol        | Conditions  | Ratings |      |           | Unit       |
|--|---------------|---|---------|------|-----------|------------|
|  |               |   | Min.    | Typ. | Max.      |            |
| Drain-source breakdown voltage             | $V_{(BR)DSS}$ | $I_D=1mA, V_{GS}=0V$  | 60      | —    | —         | V          |
| Zero gate voltage drain current            | $I_{DSS}$     | $V_{DS}=60V, V_{GS}=0V$   | —       | —    | 1.0       | $\mu A$    |
| Gate-source leakage current                | $I_{GSS}$     | $V_{GS}=\pm 20V, V_{DS}=0V$   | —       | —    | $\pm 0.1$ | $\mu A$    |
| Static drain-source on-state resistance    | $R_{DS(ON)}$  | Chip<br>$I_D=55A, V_{GS}=10V$   | —       | 2.4  | —         | m $\Omega$ |
|  |               | Terminal<br>$I_D=55A, V_{GS}=10V$   | —       | 2.9  | 3.8       | m $\Omega$ |
| Gate threshold voltage                     | $V_{TH}$      | $I_D=1mA, V_{DS}=10V$   | 2.0     | 3.0  | 4.0       | V          |
| Source-drain diode forward voltage         | $V_{SD}$      | $I_S=110A, V_{GS}=0V$   | —       | —    | 1.5       | V          |
| Total gate charge                          | $Q_g$         | $V_{DD}=48V, V_{GS}=10V, I_D=110A$<br>(Electrical characteristics of discrete MOSFET device)  | —       | 96   | —         | nC         |
| Gate to source charge                      | $Q_{gs}$      |   | —       | 25   | —         |            |
| Gate to drain charge                       | $Q_{gd}$      |   | —       | 32   | —         |            |
| Input capacitance                          | $C_{iss}$     | $V_{DS}=25V, V_{GS}=0V, f=1MHz$<br>(Electrical characteristics of discrete MOSFET device)   | —       | 5535 | —         | pF         |
| Reverse transfer capacitance               | $C_{rss}$     |   | —       | 262  | —         |            |
| Output capacitance                         | $C_{oss}$     |   | —       | 582  | —         |            |
| Turn-on delay time                         | $t_d(on)$     | $I_D=55A, V_{DD}=30V,$<br>$R_L=0.55\Omega, R_g=0\Omega,$<br>$V_{GS}(+)=10V, V_{GS}(-)=0V$<br>(Electrical characteristics of discrete MOSFET device) | —       | 10   | —         | ns         |
| Rise time                                  | $t_r$         |   | —       | 54   | —         |            |
| Turn-off delay time                        | $t_d(off)$    |   | —       | 60   | —         |            |
| Fall time                                  | $t_f$         |   | —       | 56   | —         |            |
| Source-drain diode reverse recovery time   | $t_{rr}$      | $I_F=110A, V_{GS}=0V, di/dt=100A/\mu s$   | —       | 37   | —         | ns         |
| Source-drain diode reverse recovery charge | $Q_{rr}$      |   | —       | 61   | —         | nC         |

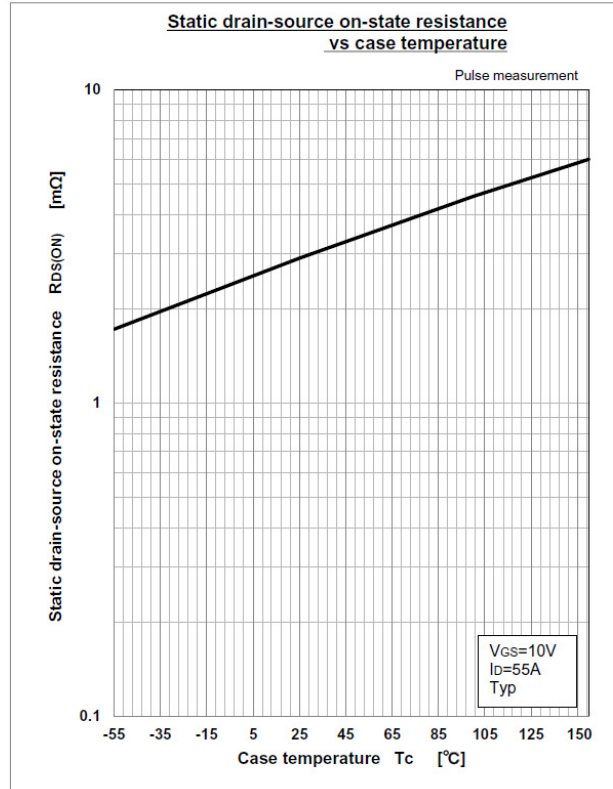
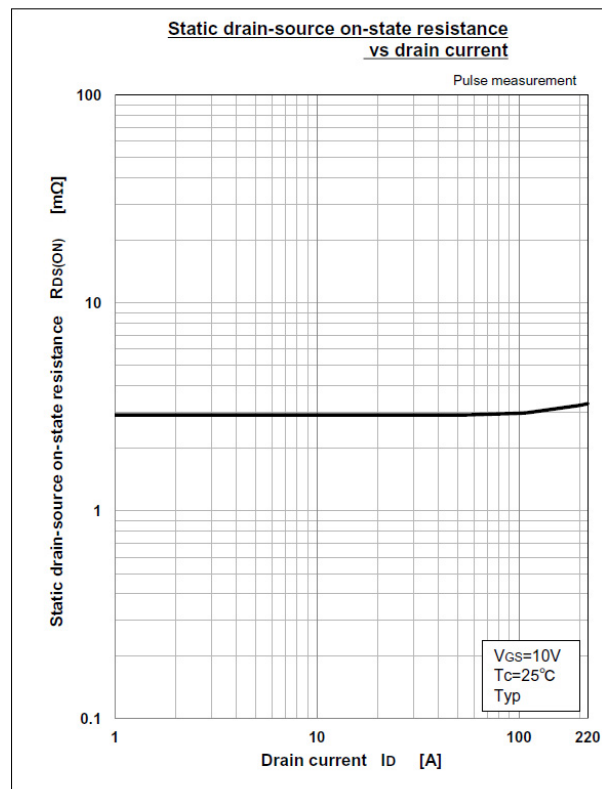
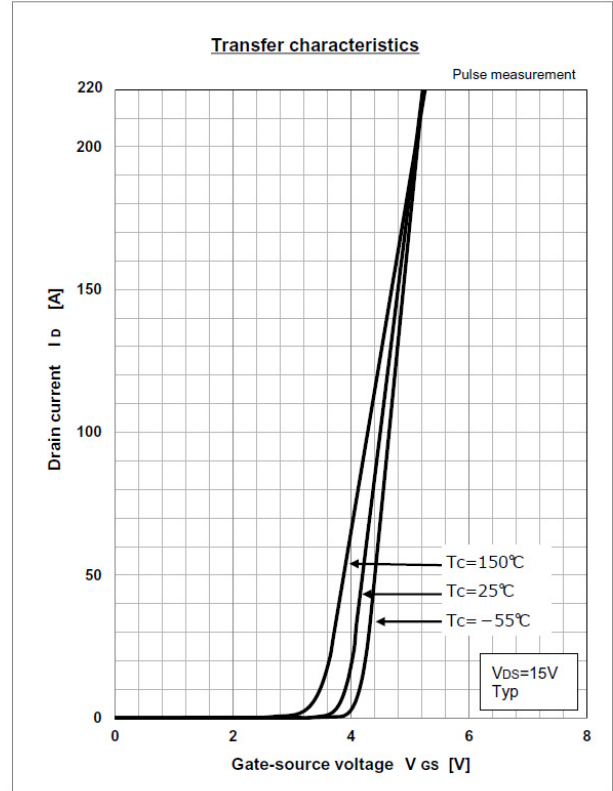
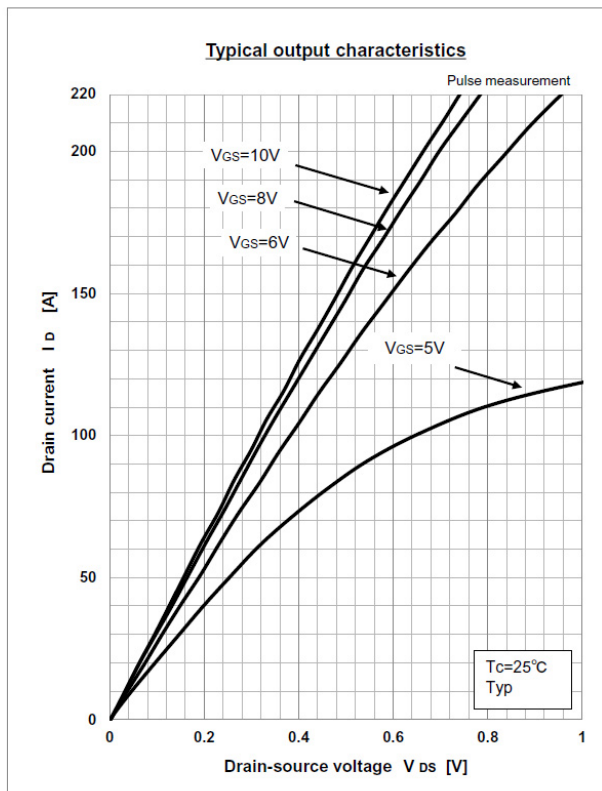
## Module

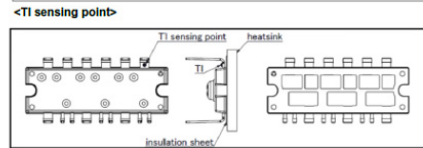
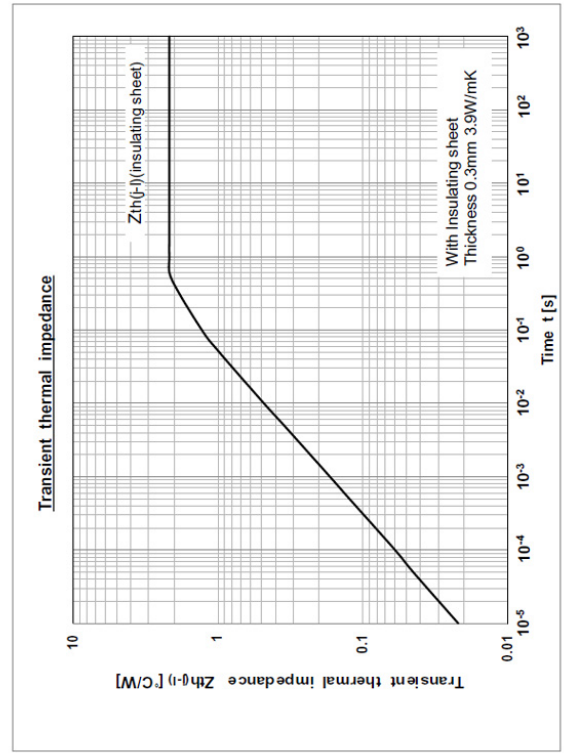
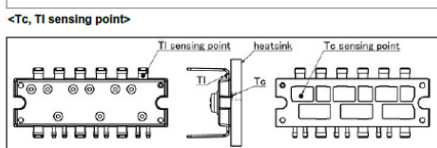
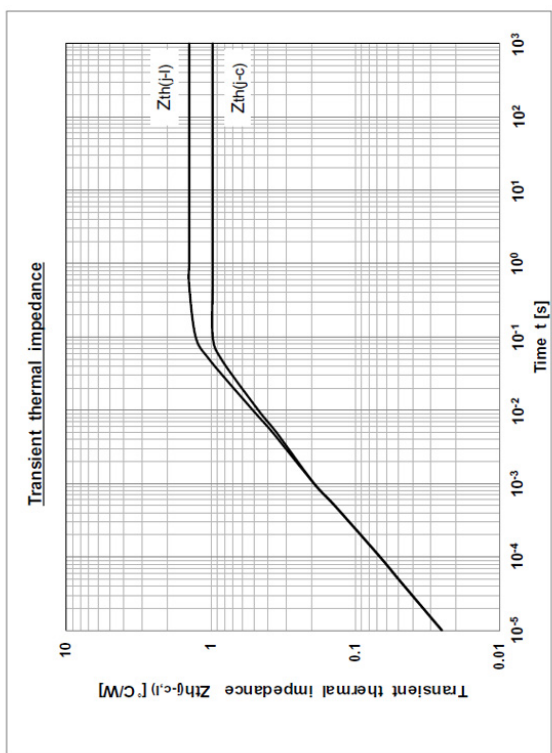
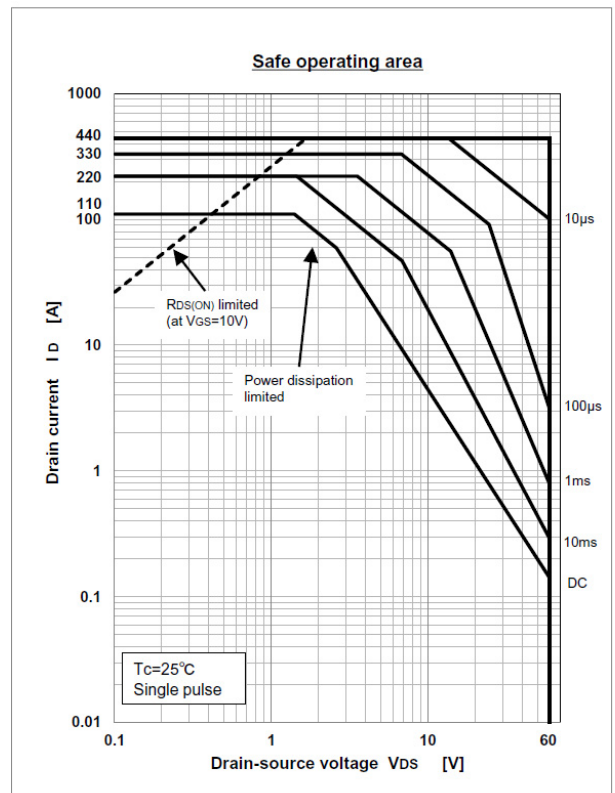
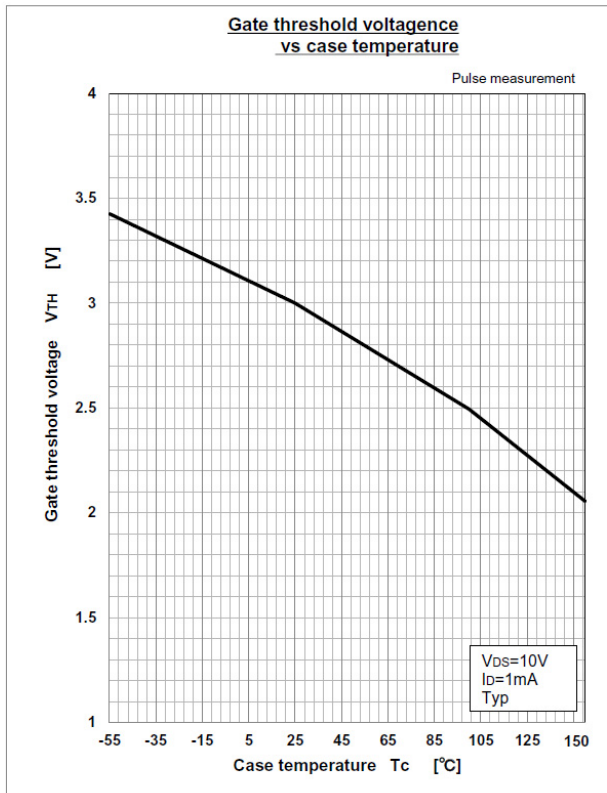
| Item               | Symbol        | Conditions   | Ratings |      |      | Unit          |
|--------------------|---------------|--|---------|------|------|---------------|
|                    |               |  | Min.    | Typ. | Max. |               |
| Thermal resistance | $R_{th(j-c)}$ | Junction to case   | —       | —    | 0.97 | $^{\circ}C/W$ |
|                    | $R_{th(j-l)}$ | Junction to lead   | —       | —    | 1.41 |               |
|                    |               | Junction to lead, With insulating sheet, Thickness 0.3mm, Thermal conductivity 3.9W/mK | —       | —    | 2.16 |               |

Note : Thermal resistance was measured at Q3

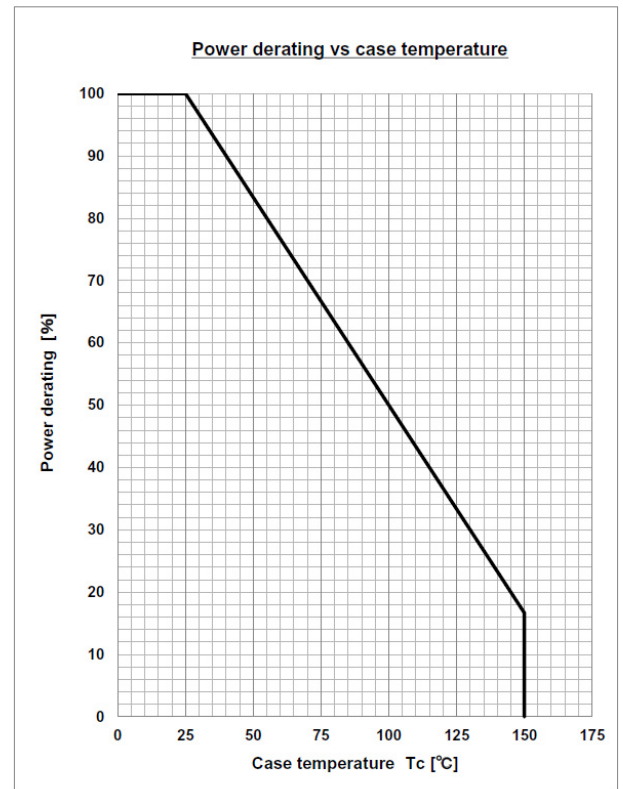
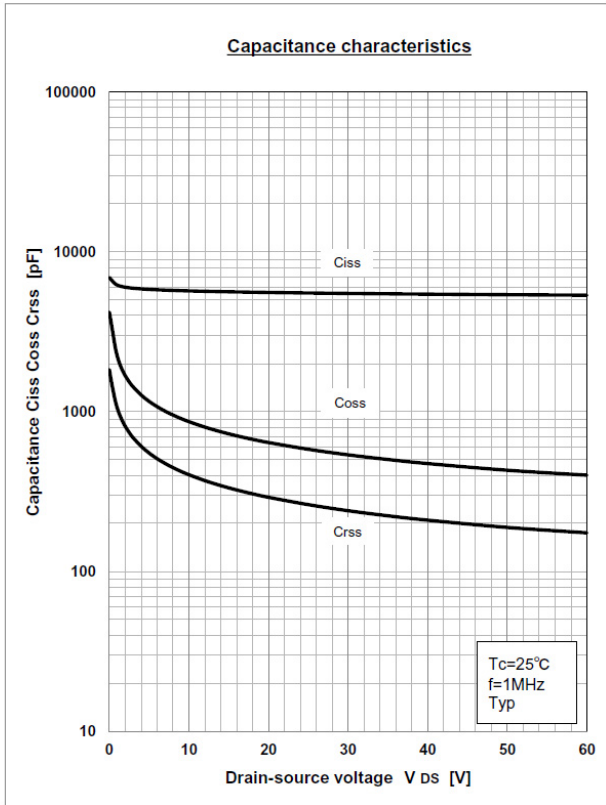
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## CHARACTERISTIC DIAGRAMS

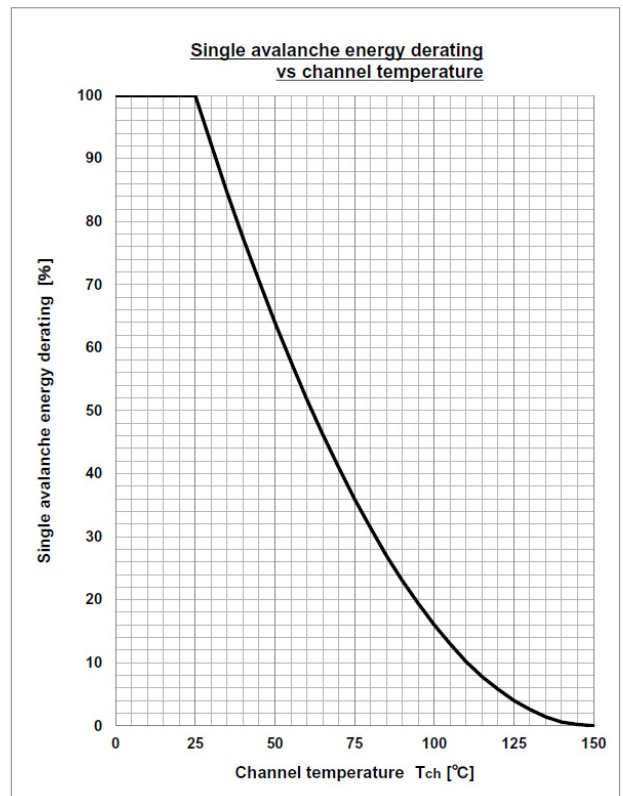
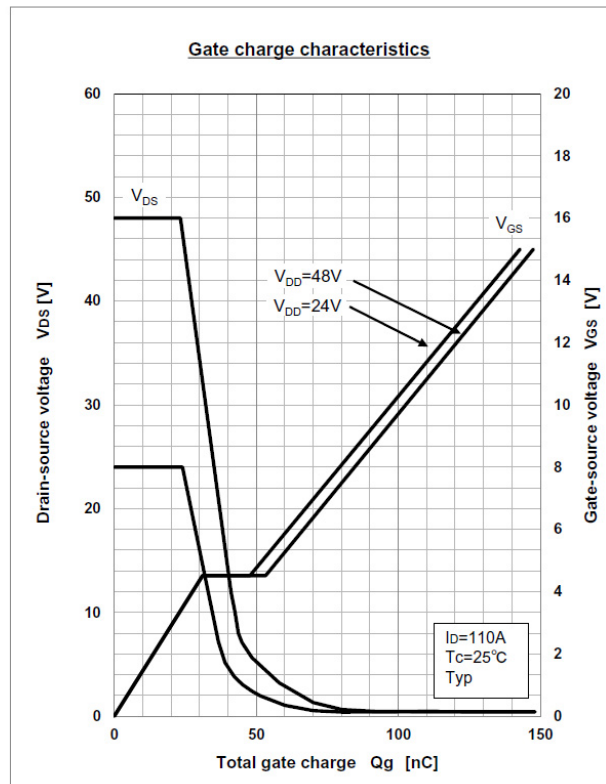




This figure shows the data of a discrete MOSFET device.



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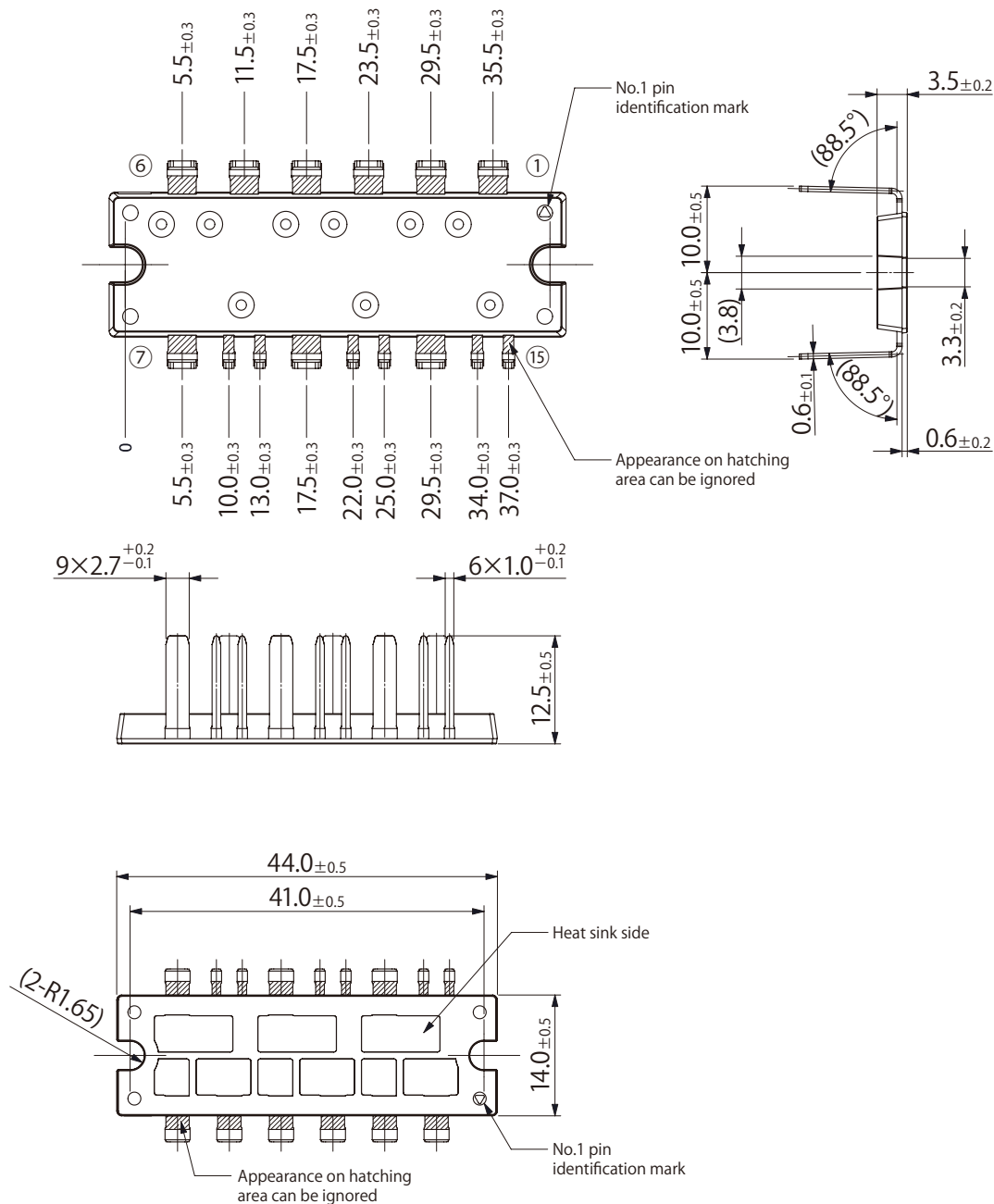


# Package Outline-Dimensions

unit : mm

F5

|            |       |
|------------|-------|
| JEDEC Code | —     |
| JEITA Code | —     |
| House Name | MG031 |



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